

General Description

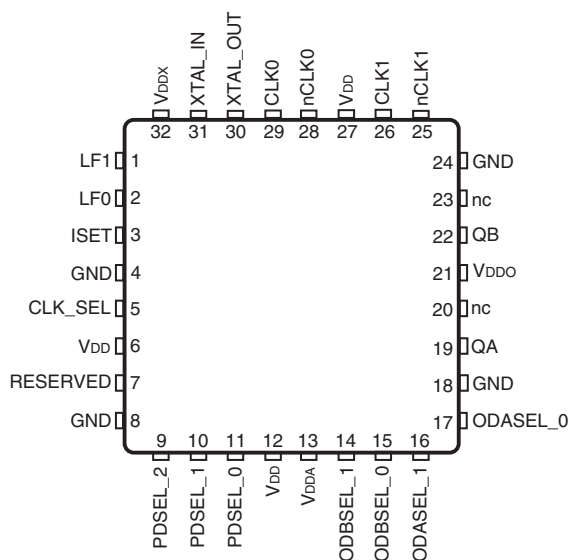


The ICS810252DI-02 is a PLL based synchronous multiplier that is optimized for PDH or SONET to Ethernet clock jitter attenuation and frequency translation. The device contains two internal frequency multiplication stages that are cascaded in series. The first stage is a VCXO PLL that is optimized to provide reference clock jitter attenuation. The second stage is a FemtoClock™ frequency multiplier that provides the low jitter, high frequency Ethernet output clock that easily meets Gigabit and 10 Gigabit Ethernet jitter requirements. Pre-divider and output divider multiplication ratios are selected using device selection control pins. The multiplication ratios are optimized to support most common clock rates used in PDH, SONET and Ethernet applications. The VCXO requires the use of an external, inexpensive pullable crystal. The VCXO uses external passive loop filter components which allows configuration of the PLL loop bandwidth and damping characteristics. The device is packaged in a space-saving 32-VFQFN package and supports industrial temperature range.

Features

- Two LVCMOS/LVTTL outputs, 14Ω output impedance
Each output supports independent frequency selection at 25MHz, 125MHz, 156.25MHz and 312.5MHz
- Two differential input pairs support the following input types: LVPECL, LVDS, LVHSTL, SSTL, HCSL
- Accepts input frequencies from: 8kHz to 155.52MHz including 8kHz, 1.544MHz, 2.048MHz, 19.44MHz, 25MHz, 77.76MHz, 125MHz and 155.52MHz
- Attenuates the phase jitter of the input clock by using a low-cost pullable fundamental mode VCXO crystal
- VCXO PLL bandwidth can be optimized for jitter attenuation and reference tracking using external loop filter connection
- FemtoClock frequency multiplier provides low jitter, high frequency output
- Absolute pull range: ±50ppm
- FemtoClock VCO frequency: 625MHz
- RMS phase jitter @ 125MHz, using a 25MHz crystal (10kHz – 20MHz): 1.3ps (maximum)
- 3.3V supply voltage
- -40°C to 85°C ambient operating temperature
- Available in lead-free (RoHS 6) package

Pin Assignment



ICS810252DI-02

32 Lead VFQFN

5mm x 5mm x 0.925mm package body

K Package

Top View

Block Diagram

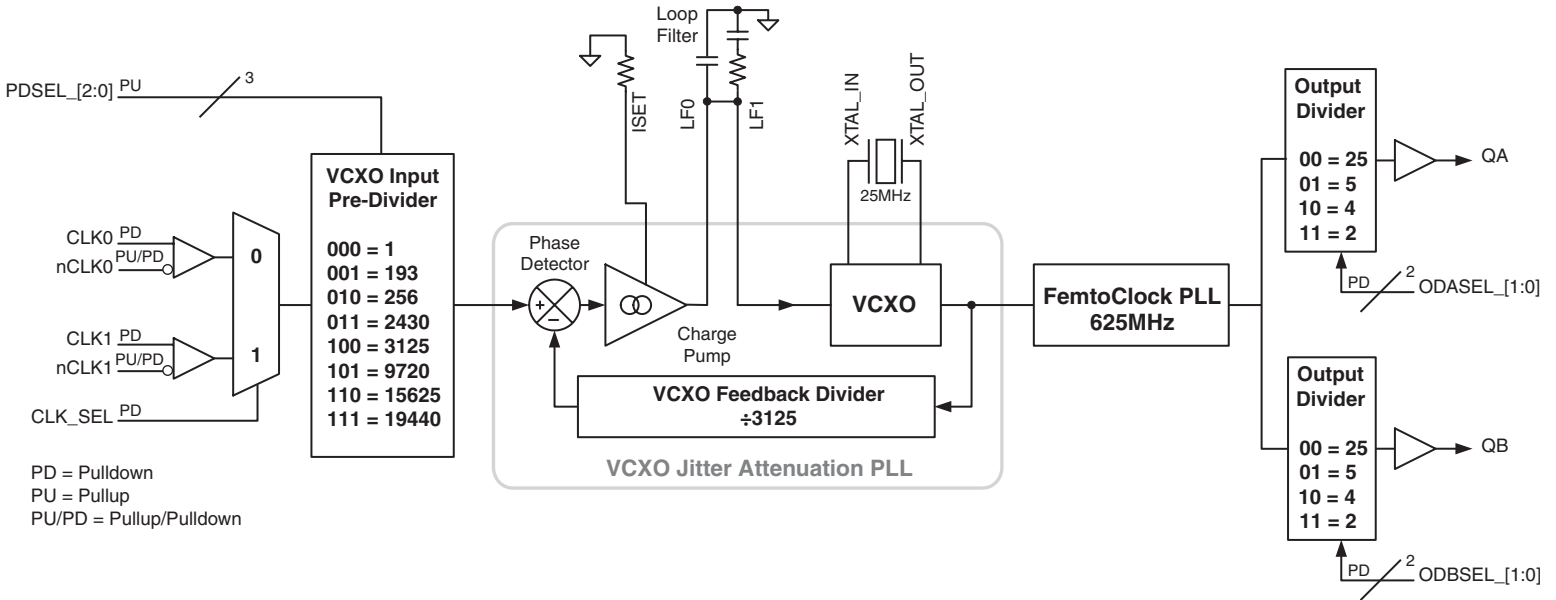


Table 1. Pin Descriptions

| Number | Name | Type | | Description |
|--------------|---------------------------|---------------------|---------------------|---|
| 1, 2 | LF1, LF0 | Analog Input/Output | | Loop filter connection node pins. LF0 is the output. LF1 is the input. |
| 3 | ISET | Analog Input/Output | | Charge pump current setting pin. |
| 4, 8, 18, 24 | GND | Power | | Power supply ground. |
| 5 | CLK_SEL | Input | Pulldown | Input clock select. When HIGH selects CLK1/nCLK1. When LOW, selects CLK0/nCLK0. LVCMOS / LVTTTL interface levels. |
| 6, 12, 27 | V _{DD} | Power | | Core supply pins. |
| 7 | RESERVED | Reserved | | Reserved pin. Do not connect. |
| 9, 10, 11 | PDSEL_2, PDSEL_1, PDSEL_0 | Input | Pullup | Pre-divider select pins. LVCMOS/LVTTTL interface levels. See Table 3A. |
| 13 | V _{DDA} | Power | | Analog supply pin. |
| 14, 15 | ODBSEL_1, ODBSEL_0 | Input | Pulldown | Frequency select pin for Bank B output. See Table 3B. LVCMOS/LVTTTL interface levels. |
| 16, 17 | ODASEL_1, ODASEL_0 | Input | Pulldown | Frequency select pin for Bank A output. See Table 3B. LVCMOS/LVTTTL interface levels. |
| 19 | QA | Output | | Single-ended Bank A clock output. LVCMOS/LVTTTL interface levels. |
| 20, 23 | nc | Unused | | No connect. |
| 21 | V _{DDO} | Power | | Output supply pin. |
| 22 | QB | Output | | Single-ended Bank B clock output. LVCMOS/LVTTTL interface levels. |
| 25 | nCLK1 | Input | Pullup/ Pulldown | Inverting differential clock input. V _{DD} /2 bias voltage when left floating. |
| 26 | CLK1 | Input | Pulldown | Non-inverting differential clock input. |
| 28 | nCLK0 | Input | Pullup/ Pulldown | Inverting differential clock input. V _{DD} /2 bias voltage when left floating. |
| 29 | CLK0 | Input | Pulldown | Non-inverting differential clock input. |
| 30, 31 | XTAL_OUT, XTAL_IN | Input | | Crystal oscillator interface. XTAL_IN is the input. XTAL_OUT is the output. |
| 32 | V _{DDX} | Power | | Power supply pin for VCXO charge pump. |

NOTE: *Pullup* and *Pulldown* refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

Table 2. Pin Characteristics

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------------|--|--|---------|---------|---------|-------|
| C _{IN} | Input Capacitance | | | 4 | | pF |
| C _{PD} | Power Dissipation Capacitance (per output) | V _{DD} = V _{DDX} = V _{DDO} = 3.465V | | 9 | 12 | pF |
| R _{PULLUP} | Input Pullup Resistor | | | 51 | | kΩ |
| R _{PULLDOWN} | Input Pulldown Resistor | | | 51 | | kΩ |
| R _{OUT} | Output Impedance | | | 14 | | Ω |

Function Tables

Table 3A. Pre-Divider Selection Function Table

| Inputs | | | Pre-Divider Value |
|---------|---------|---------|-------------------|
| PDSEL_2 | PDSEL_1 | PDSEL_0 | |
| 0 | 0 | 0 | 1 |
| 0 | 0 | 1 | 193 |
| 0 | 1 | 0 | 256 |
| 0 | 1 | 1 | 2430 |
| 1 | 0 | 0 | 3125 |
| 1 | 0 | 1 | 9720 |
| 1 | 1 | 0 | 15625 |
| 1 | 1 | 1 | 19440 (default) |

Table 3B. Output Divider Function Table

| Inputs | | Output Divider Value |
|----------|----------|----------------------|
| ODxSEL_1 | ODxSEL_0 | |
| 0 | 0 | 25 (default) |
| 0 | 1 | 5 |
| 1 | 0 | 4 |
| 1 | 1 | 2 |

Table 3C. Frequency Function Table

| Input Frequency (MHz) | Pre-Divider Value | VCXO Frequency (MHz) | FemtoClock Feedback Divider Value | FemtoClock VCO Frequency (MHz) | Output Divider Value | Output Frequency (MHz) |
|-----------------------|-------------------|----------------------|-----------------------------------|--------------------------------|----------------------|------------------------|
| 0.008 | 1 | 25 | 25 | 625 | 25 | 25 |
| 0.008 | 1 | 25 | 25 | 625 | 5 | 125 |
| 0.008 | 1 | 25 | 25 | 625 | 4 | 156.25 |
| 0.008 | 1 | 25 | 25 | 625 | 2 | 312.5 |
| 1.544 | 193 | 25 | 25 | 625 | 25 | 25 |
| 1.544 | 193 | 25 | 25 | 625 | 5 | 125 |
| 1.544 | 193 | 25 | 25 | 625 | 4 | 156.25 |
| 1.544 | 193 | 25 | 25 | 625 | 2 | 312.5 |
| 2.048 | 256 | 25 | 25 | 625 | 25 | 25 |
| 2.048 | 256 | 25 | 25 | 625 | 5 | 125 |
| 2.048 | 256 | 25 | 25 | 625 | 4 | 156.25 |
| 2.048 | 256 | 25 | 25 | 625 | 2 | 312.5 |
| 19.44 | 2430 | 25 | 25 | 625 | 25 | 25 |
| 19.44 | 2430 | 25 | 25 | 625 | 5 | 125 |
| 19.44 | 2430 | 25 | 25 | 625 | 4 | 156.25 |
| 19.44 | 2430 | 25 | 25 | 625 | 2 | 312.5 |
| 25 | 3125 | 25 | 25 | 625 | 25 | 25 |
| 25 | 3125 | 25 | 25 | 625 | 5 | 125 |
| 25 | 3125 | 25 | 25 | 625 | 4 | 156.25 |
| 25 | 3125 | 25 | 25 | 625 | 2 | 312.5 |
| 77.76 | 9720 | 25 | 25 | 625 | 25 | 25 |
| 77.76 | 9720 | 25 | 25 | 625 | 5 | 125 |
| 77.76 | 9720 | 25 | 25 | 625 | 4 | 156.25 |
| 77.76 | 9720 | 25 | 25 | 625 | 2 | 312.5 |
| 125 | 15625 | 25 | 25 | 625 | 25 | 25 |
| 125 | 15625 | 25 | 25 | 625 | 5 | 125 |
| 125 | 15625 | 25 | 25 | 625 | 4 | 156.25 |
| 125 | 15625 | 25 | 25 | 625 | 2 | 312.5 |
| 155.52 | 19440 | 25 | 25 | 625 | 25 | 25 |
| 155.52 | 19440 | 25 | 25 | 625 | 5 | 125 |
| 155.52 | 19440 | 25 | 25 | 625 | 4 | 156.25 |
| 155.52 | 19440 | 25 | 25 | 625 | 2 | 312.5 |

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

| Item | Rating |
|--|--|
| Supply Voltage, V_{DD} | 4.6V |
| Inputs, V_I XTAL_IN Other Inputs | 0V to V_{DD} -0.5V to $V_{DD} + 0.5V$ |
| Outputs, V_O | -0.5V to $V_{DD} + 0.5V$ |
| Package Thermal Impedance, θ_{JA} | 37°C/W (0 mps) |
| Storage Temperature, T_{STG} | -65°C to 150°C |

DC Electrical Characteristics

Table 4A. Power Supply DC Characteristics, $V_{DD} = V_{DDO} = V_{DDX} = 3.3V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|--------------------|----------------------------|-----------------|-----------------|---------|----------|-------|
| V_{DD} | Core Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| V_{DDA} | Analog Supply Voltage | | $V_{DD} - 0.15$ | 3.3 | V_{DD} | V |
| V_{DDO} | Output Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| V_{DDX} | Charge Pump Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| $I_{DD} + I_{DDX}$ | Power Supply Current | | | | 206 | mA |
| I_{DDA} | Analog Supply Current | | | | 15 | mA |
| I_{DDO} | Output Supply Current | No Load | | | 3 | mA |

Table 4B. LVCMOS/LVTTL DC Characteristics, $V_{DD} = V_{DDO} = V_{DDX} = 3.3V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------|-----------------------------|-------------------------------------|--------------------------------|---------|----------------|---------------|
| V_{IH} | Input High Voltage | | 2 | | $V_{DD} + 0.3$ | V |
| V_{IL} | Input Low Voltage | | -0.3 | | 0.8 | V |
| I_{IH} | Input High Current | CLK_SEL, ODASEL_[1:0], ODBSEL_[1:0] | $V_{DD} = V_{IN} = 3.465V$ | | 150 | μA |
| | | PDSEL[2:0] | $V_{DD} = V_{IN} = 3.465V$ | | 5 | μA |
| I_{IL} | Input Low Current | CLK_SEL, ODASEL_[1:0], ODBSEL_[1:0] | $V_{DD} = 3.465V, V_{IN} = 0V$ | -5 | | μA |
| | | PDSEL[2:0] | $V_{DD} = 3.465, V_{IN} = 0V$ | -150 | | μA |
| V_{OH} | Output High Voltage; NOTE 1 | | 2.6 | | | V |
| V_{OL} | Output Low Voltage; NOTE 1 | | | | 0.5 | V |

NOTE 1: Outputs terminated with 50Ω to $V_{DDO}/2$. See Parameter Measurement Information section. *Load Test Circuit diagrams*.

Table 4C. Differential DC Characteristics, $V_{DD} = V_{DDO} = V_{DDX} = 3.3V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------|-----------------------------------|---------------------------|--------------------------------|---------|-----------------|---------------|
| I_{IH} | Input High Current | CLK0/nCLK0, CLK1/nCLK1 | $V_{DD} = V_{IN} = 3.465V$ | | 150 | μA |
| I_{IL} | Input Low Current | CLK0, CLK1 | $V_{DD} = 3.465V, V_{IN} = 0V$ | -5 | | μA |
| | | nCLK0, nCLK1 | $V_{DD} = 3.465V, V_{IN} = 0V$ | -150 | | μA |
| V_{PP} | Peak-to-Peak Input Voltage | | 0.15 | | 1.3 | V |
| V_{CMR} | Common Mode Input Voltage; NOTE 1 | | GND + 0.5 | | $V_{DD} - 0.85$ | V |

NOTE 1: Common mode voltage is defined as V_{IH} .

AC Electrical Characteristics

Table 5. AC Characteristics, $V_{DD} = V_{DDO} = V_{DDX} = 3.3V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------------------|--|---|---------|---------|---------|-------|
| f_{IN} | Input Frequency | | 0.008 | | 155.52 | MHz |
| f_{OUT} | Output Frequency | | 25 | | 312.5 | MHz |
| $f_{jit}(\emptyset)$ | RMS Phase Jitter, (Random), NOTE 1, 2 | 125MHz f_{OUT} , 25MHz crystal, Integration Range: 10kHz – 20MHz | | 1.05 | 1.3 | ps |
| $t_{sk(o)}$ | Output Skew; NOTE 3, 4 | | | | 200 | ps |
| odc | Output Duty Cycle | $f_{OUT} \leq 156.25\text{MHz}$ | 45 | | 55 | % |
| t_R / t_F | Output Rise/Fall Time | 20% to 80% | 200 | | 800 | ps |
| t_{LOCK} | VCXO & FemtoClock PLL Lock Time; NOTE 5 | Reference Clock Input is $\pm 50\text{ppm}$ from Nominal Frequency | | | 2.5 | S |

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE: Characterized with outputs at the same frequency using the loop filter components for the mid loop bandwidth. Refer to VCXO-PLL Loop Bandwidth Selection Table.

NOTE 1: Refer to the Phase Noise Plot.

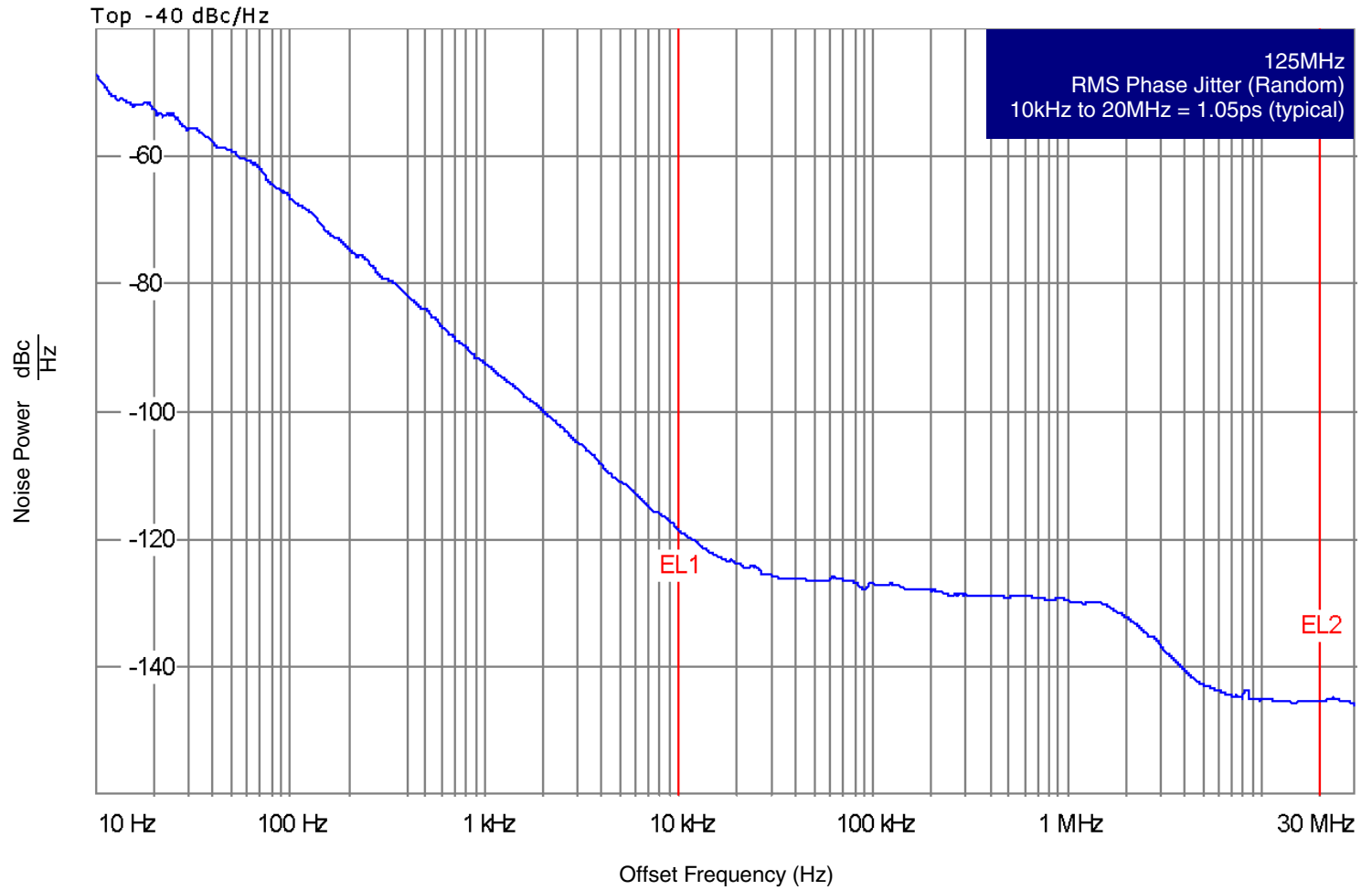
NOTE 2: Not tested in production.

NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

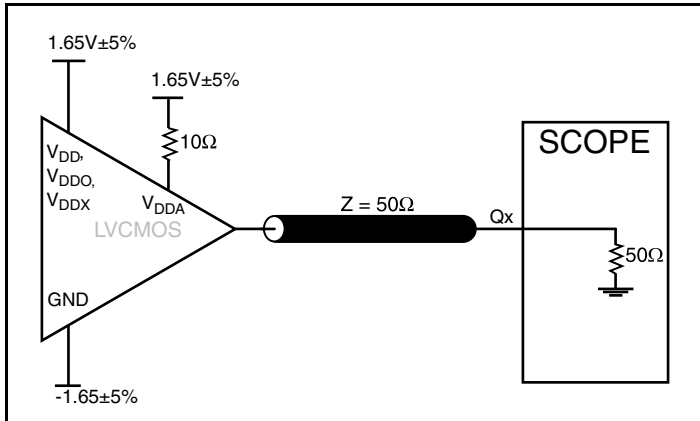
NOTE 4: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at $V_{DDO}/2$.

NOTE 5: Lock Time measured from power-up to stable output frequency.

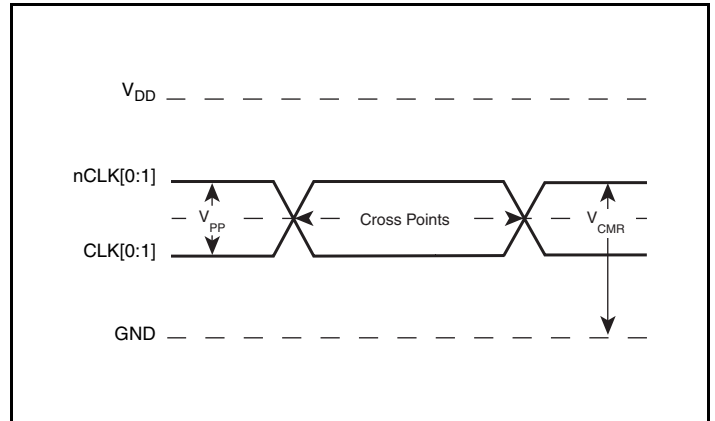
Typical Phase Noise at 125MHz



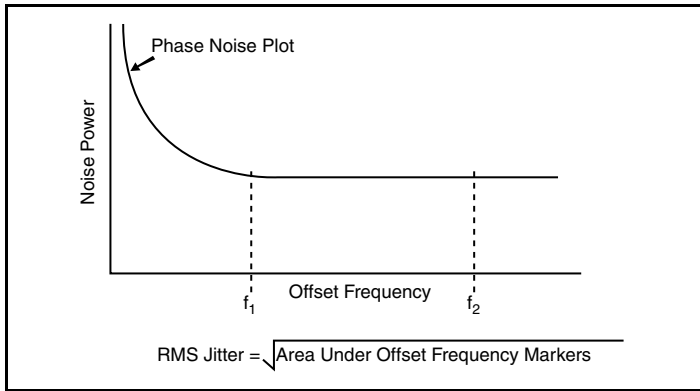
Parameter Measurement Information



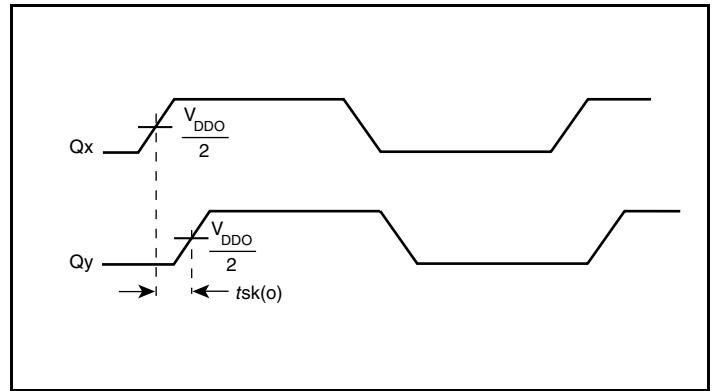
3.3V Output Load AC Test Circuit



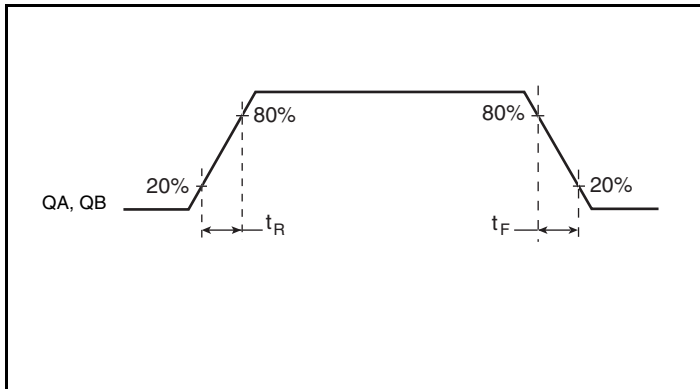
Differential Input Level



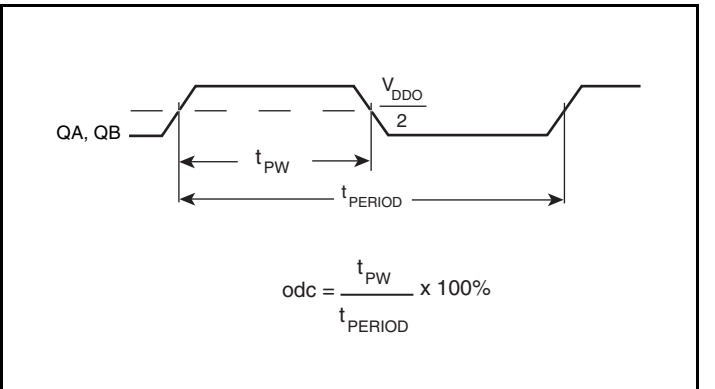
RMS Phase Jitter



Output Skew

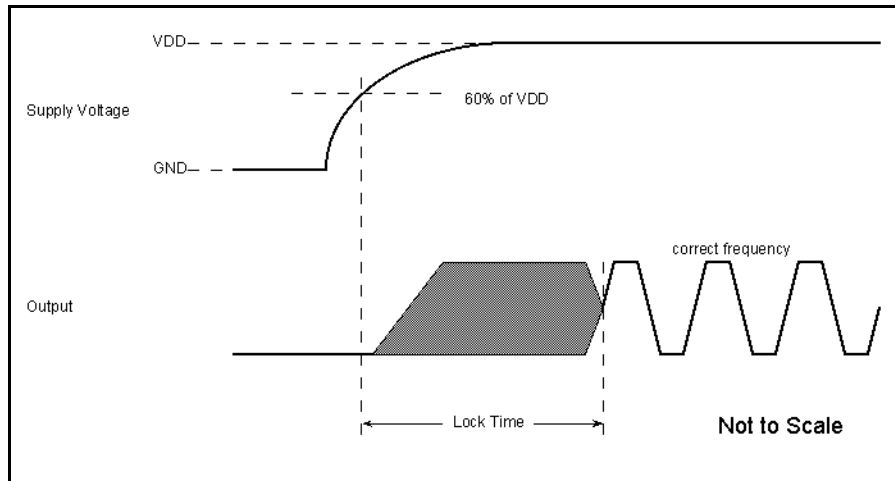


Output Rise/Fall Time



Output Duty Cycle/Pulse Width/Period

Parameter Measurement Information, continued



VCXO & FemtoClock PLL Lock Time

Application Information

Power Supply Filtering Technique

As in any high speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. The ICS810252DI-02 provides separate power supplies to isolate any high switching noise from the outputs to the internal PLL. V_{DD} , V_{DDA} , V_{DDO} and V_{DDX} should be individually connected to the power supply plane through vias, and $0.01\mu\text{F}$ bypass capacitors should be used for each pin. *Figure 1* illustrates this for a generic V_{DD} pin and also shows that V_{DDA} requires that an additional 10Ω resistor along with a $10\mu\text{F}$ bypass capacitor be connected to the V_{DDA} pin.

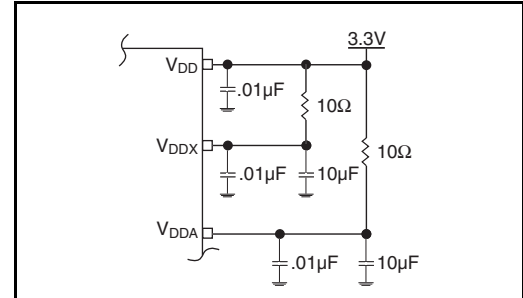


Figure 1. Power Supply Filtering

Wiring the Differential Input to Accept Single-Ended Levels

Figure 2 shows how a differential input can be wired to accept single ended levels. The reference voltage $V_{REF} = V_{DD}/2$ is generated by the bias resistors $R1$ and $R2$. The bypass capacitor ($C1$) is used to help filter noise on the DC bias. This bias circuit should be located as close to the input pin as possible. The ratio of $R1$ and $R2$ might need to be adjusted to position the V_{REF} in the center of the input voltage swing. For example, if the input clock swing is 2.5V and $V_{DD} = 3.3\text{V}$, $R1$ and $R2$ value should be adjusted to set V_{REF} at 1.25V . The values below are for when both the single ended swing and V_{DD} are at the same voltage. This configuration requires that the sum of the output impedance of the driver (R_o) and the series resistance (R_s) equals the transmission line impedance. In addition, matched termination at the input will attenuate the signal in half. This can be done in one of two ways. First, $R3$ and $R4$ in parallel should equal the transmission

line impedance. For most 50Ω applications, $R3$ and $R4$ can be 100Ω . The values of the resistors can be increased to reduce the loading for slower and weaker LVCMOS driver. When using single ended signaling, the noise rejection benefits of differential signaling are reduced. Even though the differential input can handle full rail LVCMOS signaling, it is recommended that the amplitude be reduced. The datasheet specifies a lower differential amplitude, however this only applies to differential signals. For single-ended applications, the swing can be larger, however V_{IL} cannot be less than -0.3V and V_{IH} cannot be more than $V_{DD} 0.3\text{V}$. Though some of the recommended components might not be used, the pads should be placed in the layout. They can be utilized for debugging purposes. The datasheet specifications are characterized and guaranteed by using a differential signal.

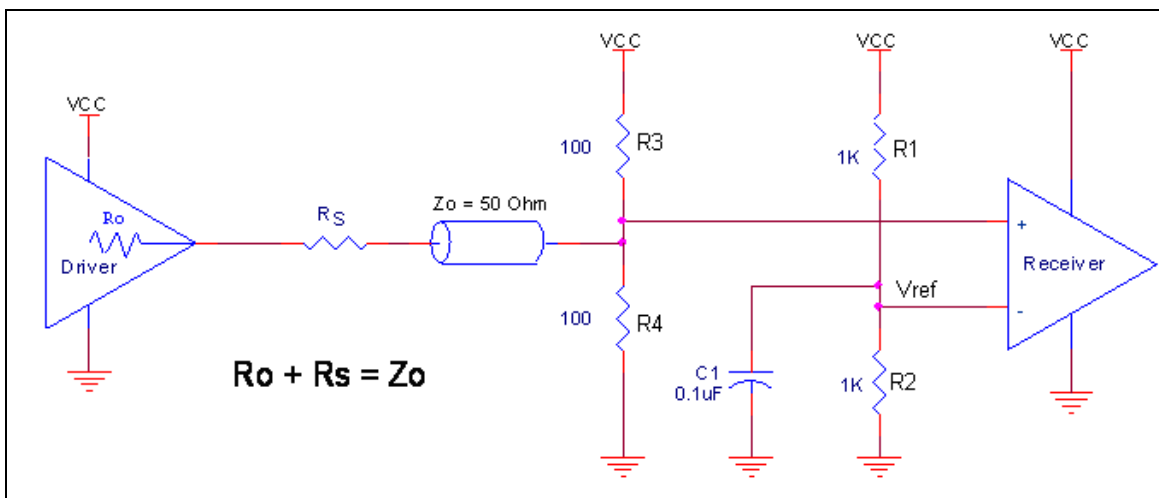


Figure 2. Recommended Schematic for Wiring a Differential Input to Accept Single-ended Levels

Differential Clock Input Interface

The CLK /nCLK accepts LVDS, LVPECL, LVHSTL, SSTL, HCSL and other differential signals. Both differential signals must meet the V_{PP} and V_{CMR} input requirements. Figures 3A to 3F show interface examples for the CLK/nCLK input driven by the most common driver types. The input interfaces suggested here are examples only.

Please consult with the vendor of the driver component to confirm the driver termination requirements. For example, in Figure 3A, the input termination applies for IDT open emitter LVHSTL drivers. If you are using an LVHSTL driver from another vendor, use their termination recommendation.

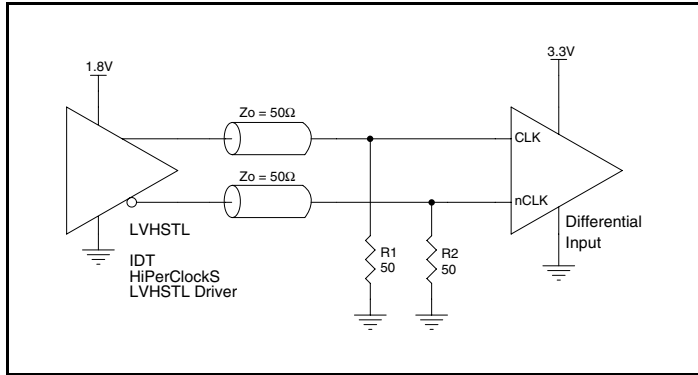


Figure 3A. CLK/nCLK Input Driven by an IDT Open Emitter LVHSTL Driver

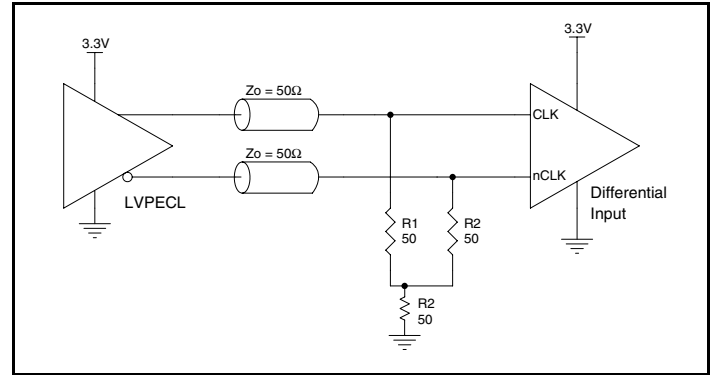


Figure 3B. CLK/nCLK Input Driven by a 3.3V LVPECL Driver

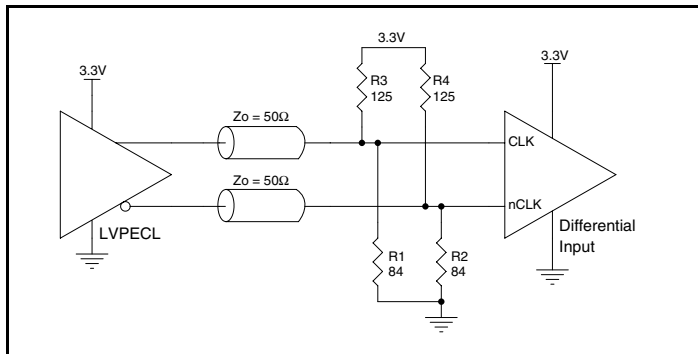


Figure 3C. CLK/nCLK Input Driven by a 3.3V LVPECL Driver

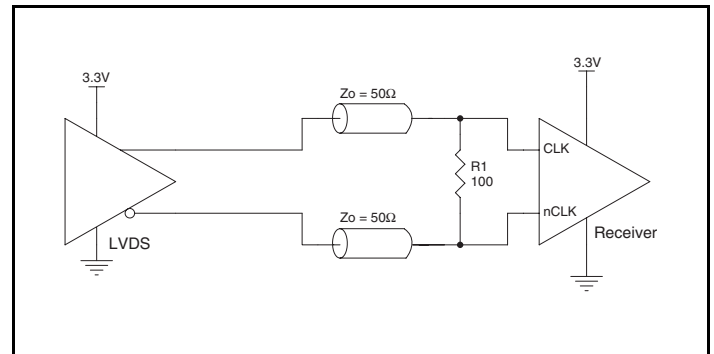


Figure 3D. CLK/nCLK Input Driven by a 3.3V LVDS Driver

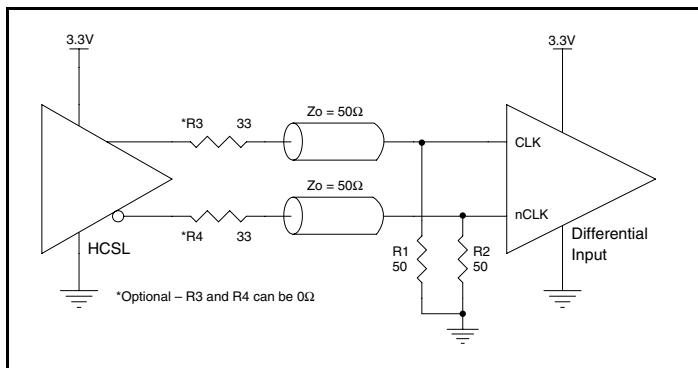


Figure 3E. CLK/nCLK Input Driven by a 3.3V HCSL Driver

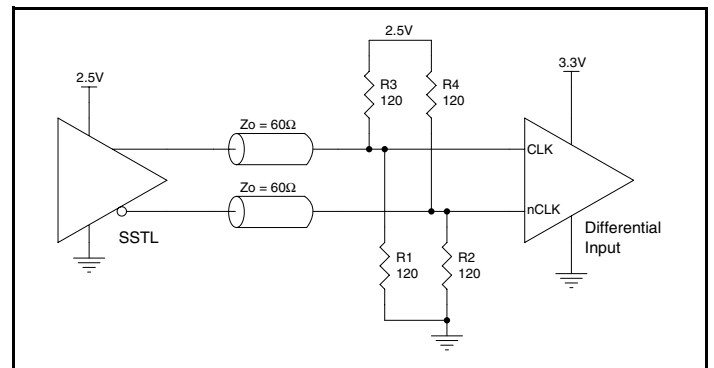


Figure 3F. CLK/nCLK Input Driven by a 2.5V SSTL Driver

Recommendations for Unused Input and Output Pins

Inputs:

CLK/nCLK Inputs

For applications not requiring the use of the differential input, both CLK and nCLK can be left floating. Though not required, but for additional protection, a 1k Ω resistor can be tied from CLK to ground.

LVC MOS Control Pins

All control pins have internal pullups or pulldowns; additional resistance is not required but can be added for additional protection. A 1k Ω resistor can be used.

Outputs:

LVC MOS Outputs

All unused LVC MOS output can be left floating. There should be no trace attached.

VFQFN EPAD Thermal Release Path

In order to maximize both the removal of heat from the package and the electrical performance, a land pattern must be incorporated on the Printed Circuit Board (PCB) within the footprint of the package corresponding to the exposed metal pad or exposed heat slug on the package, as shown in *Figure 4*. The solderable area on the PCB, as defined by the solder mask, should be at least the same size/shape as the exposed pad/slug area on the package to maximize the thermal/electrical performance. Sufficient clearance should be designed on the PCB between the outer edges of the land pattern and the inner edges of pad pattern for the leads to avoid any shorts.

While the land pattern on the PCB provides a means of heat transfer and electrical grounding from the package to the board through a solder joint, thermal vias are necessary to effectively conduct from the surface of the PCB to the ground plane(s). The land pattern must be connected to ground through these vias. The vias act as “heat pipes”. The number of vias (i.e. “heat pipes”) are application specific

and dependent upon the package power dissipation as well as electrical conductivity requirements. Thus, thermal and electrical analysis and/or testing are recommended to determine the minimum number needed. Maximum thermal and electrical performance is achieved when an array of vias is incorporated in the land pattern. It is recommended to use as many vias connected to ground as possible. It is also recommended that the via diameter should be 12 to 13mils (0.30 to 0.33mm) with 1oz copper via barrel plating. This is desirable to avoid any solder wicking inside the via during the soldering process which may result in voids in solder between the exposed pad/slug and the thermal land. Precautions should be taken to eliminate any solder voids between the exposed heat slug and the land pattern. Note: These recommendations are to be used as a guideline only. For further information, please refer to the Application Note on the Surface Mount Assembly of Amkor’s Thermally/Electrically Enhance Leadframe Base Package, Amkor Technology.

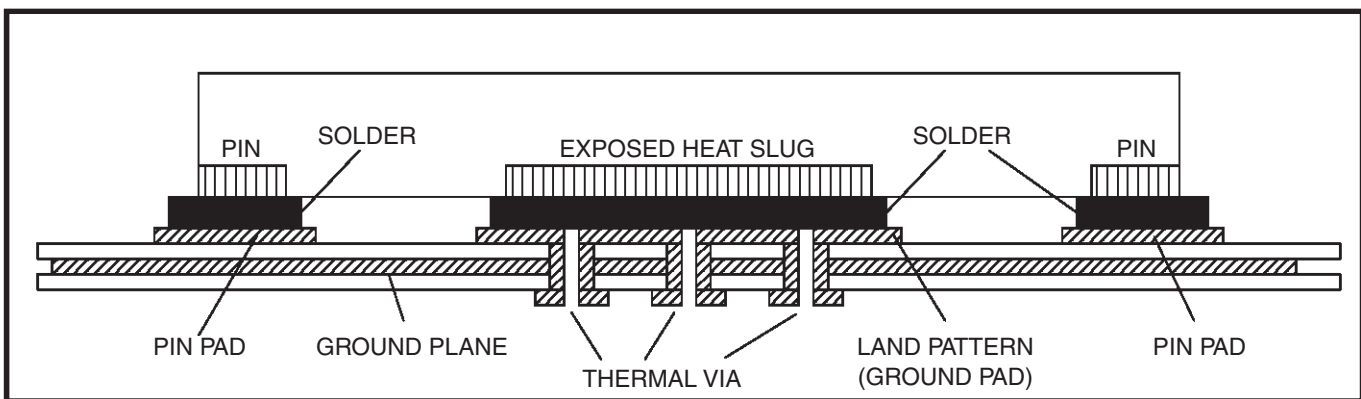


Figure 4. P.C. Assembly for Exposed Pad Thermal Release Path – Side View (drawing not to scale)

Schematic Example

Figure 5 shows an example of the 810252DI-02 application schematic. In this example, the device is operated at $V_{DD} = 3.3V$. The decoupling capacitors should be located as close as possible to the power pin. The input is driven by a 3.3V LVPECL driver. An optional

3-pole filter can also be used for additional spur reduction. It is recommended that the loop filter components be laid out for the 3-pole option. This will also allow the 2-pole filter to be used.

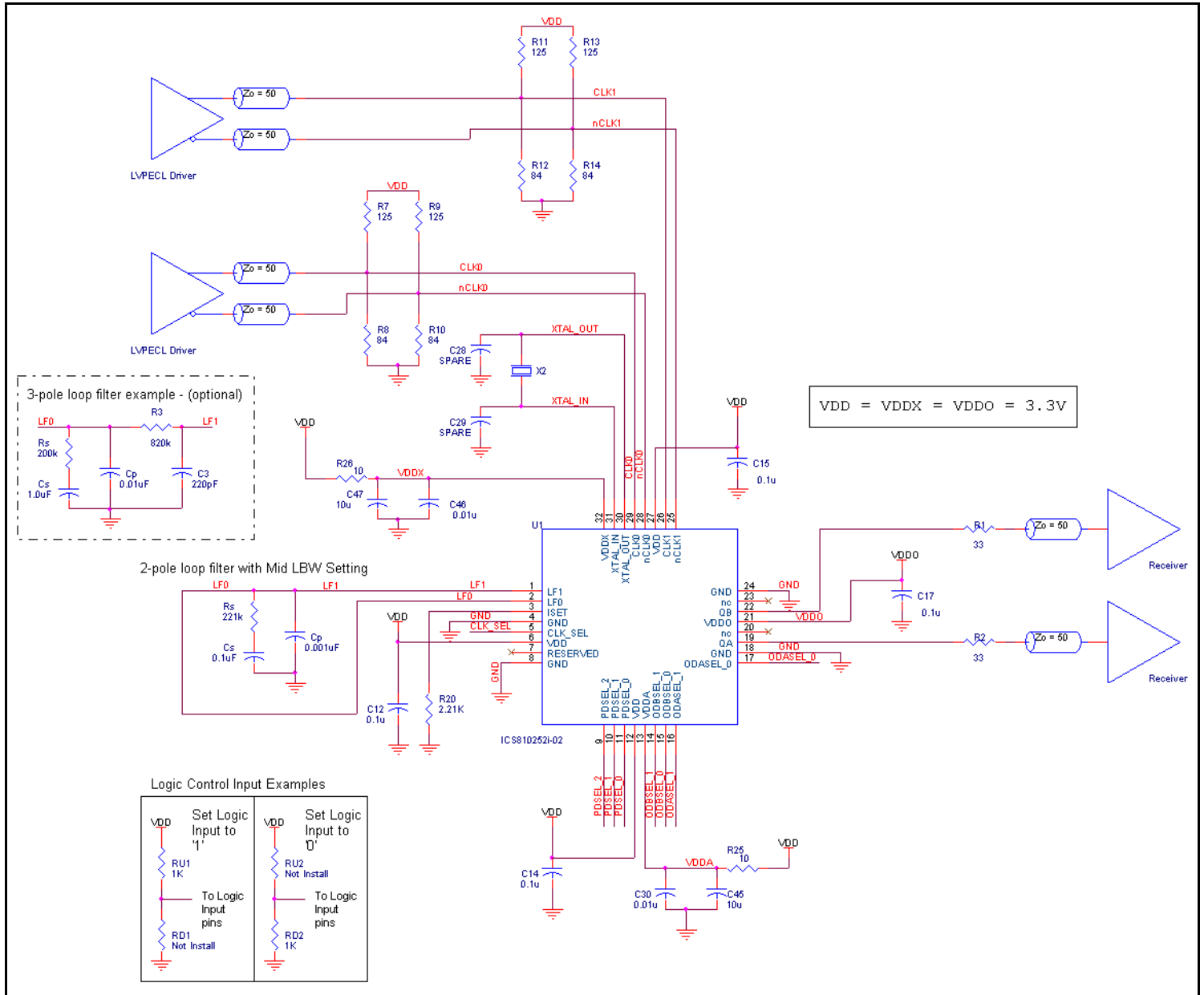


Figure 5. ICS810252DI-02 Schematic Example

VCXO-PLL EXTERNAL COMPONENTS

Choosing the correct external components and having a proper printed circuit board (PCB) layout is a key task for quality operation of the VCXO-PLL. In choosing a crystal, special precaution must be taken with the package and load capacitance (C_L). In addition, frequency, accuracy and temperature range must also be considered. Since the pulling range of a crystal also varies with the package, it is recommended that a metal-canned package like HC49 be used. Generally, a metal-canned package has a larger pulling range than a surface mounted device (SMD). For crystal selection information, refer to the *VCXO Crystal Selection Application Note*.

The crystal's load capacitance C_L characteristic determines its resonating frequency and is closely related to the VCXO tuning range. The total external capacitance seen by the crystal when installed on a board is the sum of the stray board capacitance, IC package lead capacitance, internal varactor capacitance and any installed tuning capacitors (C_{TUNE}).

If the crystal's C_L is greater than the total external capacitance, the VCXO will oscillate at a higher frequency than the crystal specification. If the crystal's C_L is lower than the total external capacitance, the VCXO will oscillate at a lower frequency than the crystal specification. In either case, the absolute tuning range is reduced. The correct value of C_L is dependent on the characteristics of the VCXO. The recommended C_L in the Crystal Parameter Table balances the tuning range by centering the tuning curve.

VCXO Characteristics Table

| Symbol | Parameter | Typical | Units |
|---------------|---------------------------|---------|-------|
| k_{VCXO} | VCXO Gain | 16,700 | kHz/V |
| C_{V_LOW} | Low Varactor Capacitance | 9.8 | pF |
| C_{V_HIGH} | High Varactor Capacitance | 22.9 | pF |

VCXO-PLL Loop Bandwidth Selection Table

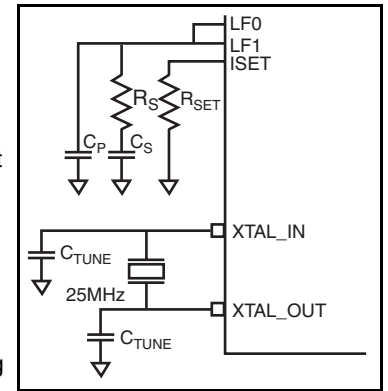
| Bandwidth | Crystal Frequency (MHz) | R_S (k Ω) | C_S (μ F) | C_P (μ F) | R_{SET} (k Ω) |
|--------------|-------------------------|---------------------|------------------|------------------|-------------------------|
| 10Hz (Low) | 25 | 121 | 1.0 | 0.01 | 9.09 |
| 90Hz (Mid) | 25 | 221 | 0.1 | 0.001 | 2.21 |
| 300Hz (High) | 25 | 680 | 0.1 | 0.0001 | 2.21 |

Crystal Characteristics

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------------------|--------------------------------------|-----------------|-------------|---------|------------------|--------------|
| | Mode of Oscillation | | Fundamental | | | |
| f_N | Frequency | | | 25 | | MHz |
| f_T | Frequency Tolerance | | | | ± 20 | ppm |
| f_S | Frequency Stability | | | | ± 20 | ppm |
| | Operating Temperature Range | | -40 | | 85 | $^{\circ}$ C |
| C_L | Load Capacitance | | | 10 | | pF |
| C_O | Shunt Capacitance | | | 4 | | pF |
| C_O / C_1 | Pullability Ratio | | | 220 | 240 | |
| F_{L_3OVT} | 3 RD Overtone F_L | | 200 | | | ppm |
| $F_{L_3OVT_spurs}$ | 3 RD Overtone F_L Spurs | | 200 | | | ppm |
| ESR | Equivalent Series Resistance | | | | 20 | Ω |
| | Drive Level | | | | 1 | mW |
| | Aging @ 25 $^{\circ}$ C | | | | ± 3 per year | ppm |

The frequency of oscillation in the third overtone mode is not necessarily at exactly three times the fundamental frequency. The mechanical properties of the quartz element dictate the position of the overtones relative to the fundamental. The oscillator circuit may excite both the fundamental and overtone modes simultaneously. This will cause a nonlinearity in the tuning curve. This potential problem is why VCXO crystals are required to be tested for absence of any activity inside a ± 200 ppm window at three times the fundamental frequency. Refer to F_{L_3OVT} and $F_{L_3OVT_spurs}$ in the crystal Characteristics table.

The crystal and external loop filter components should be kept as close as possible to the device. Loop filter and crystal traces should be kept short and separated from each other. Other signal traces should be kept separate and not run underneath the device, loop filter or crystal components.



Reliability Information

Table 6. θ_{JA} vs. Air Flow Table for a 32 Lead VFQFN

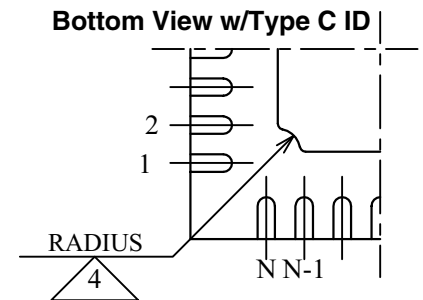
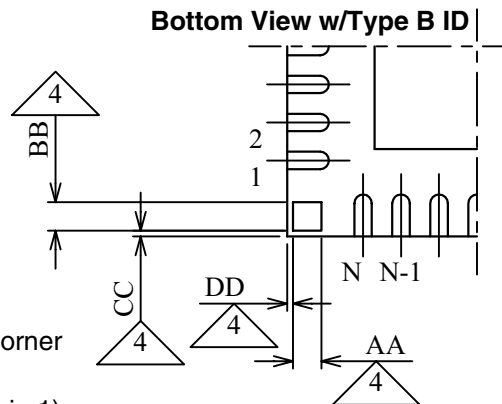
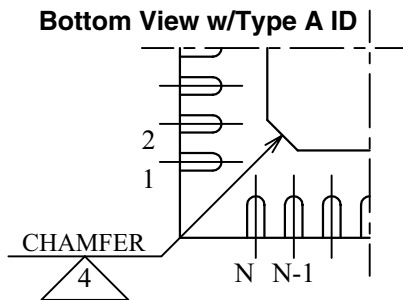
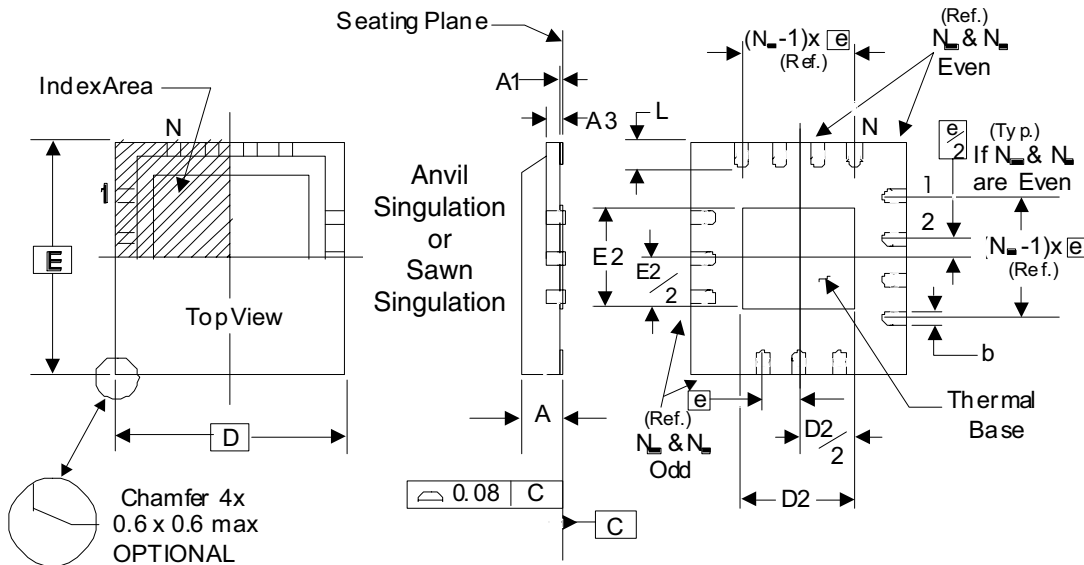
| θ_{JA} vs. Air Flow | | | |
|---|----------|----------|------------|
| Meters per Second | 0 | 1 | 2.5 |
| Multi-Layer PCB, JEDEC Standard Test Boards | 37.0°C/W | 32.4°C/W | 29°C/W |

Transistor Count

The transistor count for ICS810252DI-02 is: 6673

Package Outline and Package Dimensions

Package Outline - K Suffix for 32 Lead VFQFN



There are 3 methods of indicating pin 1 corner at the back of the VFQFN package are:

1. Type A: Chamfer on the paddle (near pin 1)
2. Type B: Dummy pad between pin 1 and N.
3. Type C: Mouse bite on the paddle (near pin 1)

Table 7. Package Dimensions

| JEDEC Variation: VHHD-2/-4 | | | |
|---------------------------------|------------|---------|---------|
| All Dimensions in Millimeters | | | |
| Symbol | Minimum | Nominal | Maximum |
| N | 32 | | |
| A | 0.80 | | 1.00 |
| A1 | 0 | | 0.05 |
| A3 | 0.25 Ref. | | |
| b | 0.18 | 0.25 | 0.30 |
| N _D & N _E | 8 | | |
| D & E | 5.00 Basic | | |
| D2 & E2 | 3.0 | | 3.3 |
| e | 0.50 Basic | | |
| L | 0.30 | 0.40 | 0.50 |

Reference Document: JEDEC Publication 95, MO-220

NOTE: The following package mechanical drawing is a generic drawing that applies to any pin count VFQFN package. This drawing is not intended to convey the actual pin count or pin layout of this device. The pin count and pinout are shown on the front page. The package dimensions are in Table 7.

Ordering Information

Table 8. Ordering Information

| Part/Order Number | Marking | Package | Shipping Packaging | Temperature |
|-------------------|-------------|---------------------------|--------------------|---------------|
| 810252DKI-02LF | ICS252DI02L | "Lead-Free" 32 Lead VFQFN | Tray | -40°C to 85°C |
| 810252DKI-02LFT | ICS252DI02 | "Lead-Free" 32 Lead VFQFN | 2500 Tape & Reel | -40°C to 85°C |

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

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